

IN THE CLAIMS

1. (Original) A nonvolatile semiconductor memory device comprising:

- a semiconductor substrate;
- a first transistor formed in a peripheral circuit portion of the semiconductor substrate,
- a gate electrode of the first transistor having a first gate length;
- a second transistor formed in a memory cell portion of the semiconductor substrate, a gate electrode of the second transistor having a second gate length shorter than the first gate length; and
- a first insulating film formed above at least the memory cell portion, the first insulating film covering the second transistor and having a property which makes it difficult for an oxidizing agent to pass therethrough.

2-18. (Canceled)